

Application No. 09/920,755

Amendments to the Specification

Please replace the paragraph beginning on page 30, line 7, with the following rewritten paragraph:

The above methods and materials may be appropriately used as the method for forming the optical element 12 of the light-emitting device ~~1000~~ 2000 and the materials for forming each layer. These methods, materials, and configurations are also applied to other embodiments described later.

Please replace the paragraph beginning on page 31, line 24, with the following rewritten paragraph:

(a) According to the light-emitting device 2000 of the present embodiment, the anode 20 and the cathode 30 are electrically connected through ~~the light-emitting section 14~~ the light-emitting layer 50 with which the opening 40a in the insulating layer 40 is filled. The region through which current flows is specified by the opening 40a. Therefore, the insulating layer 40 functions as a current blocking layer, whereby current can be efficiently supplied to the light-emitting region and light emission efficiency can be increased. The light-emitting region can be set while being positioned with the core layer 70 by specifying the region to which current is supplied by the current blocking layer (insulating layer 40). This increases the efficiency of optical connection with the waveguide section 200.

Please replace the paragraph beginning on page 33, line 17, with the following rewritten paragraph:

According to the light-emitting device ~~1000~~ 2000 of the present embodiment, the light-emitting section 100 and the waveguide section 200 can be combined with high connective efficiency, whereby emitted light with high efficiency can be obtained.

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Please replace the paragraph beginning on page 33, line 22, with the following rewritten paragraph:

(d) In the present embodiment, the optical element 12 can be formed using either an organic material or an inorganic material. Therefore, since the light-emitting device is not affected by the irregular state or impurities at the boundary between the medium layers in the optical element as in the case of using a semiconductor as the material for the optical element, excellent characteristics by the incomplete photonic band gap can be obtained.

Please replace the paragraph beginning on page 39, line 4, with the following rewritten paragraph:

Fig. ~~5~~13 shows an example in which the optical element 12 is formed in the electron transport layer 28. However, in the case where the cathode 30 is formed using a material other than a metal such as a diamond, the optical element may be formed by the electron transport layer 28 and the cathode 30. In the case where the electron transport layer 28 is not formed, the optical element may be formed by the cathode 30 and the light-emitting layer 50.